



PJQ4463AP

60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-4.2 A

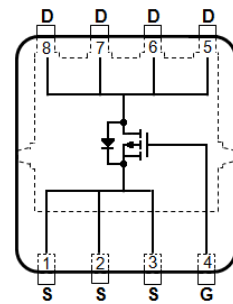
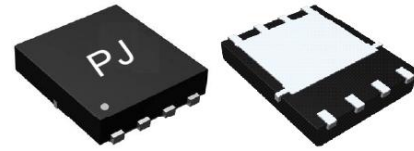
Features

- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-6A < 68m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-3A < 85m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN3333-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026

DFN3333-8L



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_A=25^\circ\text{C}$	I_D	-4.2	A
	$T_A=70^\circ\text{C}$		-3.4	
Pulsed Drain Current ^(Note 1)		I_{DM}	-16.8	
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	2.1	W
Power Dissipation	$T_A=70^\circ\text{C}$		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ\text{C}$
Typical Thermal Resistance Junction to Ambient, $t \leq 10s$ ^(Note 5)		$R_{\theta JA}$	59.5	$^\circ\text{C/W}$

- Limited only By Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.53	-2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-6A$	-	55	68	m Ω
		$V_{GS}=-4.5V, I_D=-3A$	-	71	85	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V$	-	-	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	$V_{DS}=-30V, I_D=-6A,$ $V_{GS}=-10V$ (Note 3)	-	17	-	nC
Gate-Source Charge	Q_{gs}		-	2.8	-	
Gate-Drain Charge	Q_{gd}		-	3.6	-	
Input Capacitance	C_{iss}	$V_{DS}=-30V, V_{GS}=0V,$ $f=1.0\text{MHz}$	-	879	-	pF
Output Capacitance	C_{oss}		-	70	-	
Reverse Transfer Capacitance	C_{rss}		-	47	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=-30V, I_D=-1A,$ $V_{GS}=-10V, R_G=6\Omega$ (Note 3)	-	8.4	-	ns
Turn-On Rise Time	t_r		-	30	-	
Turn-Off Delay Time	$t_{d(off)}$		-	52	-	
Turn-Off Fall Time	t_f		-	16	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	-4.2	A
Diode Forward Voltage	V_{SD}	$I_S=-1A, V_{GS}=0V$	-	-0.73	-1	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.
4. The maximum current rating is package limited
5. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
6. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

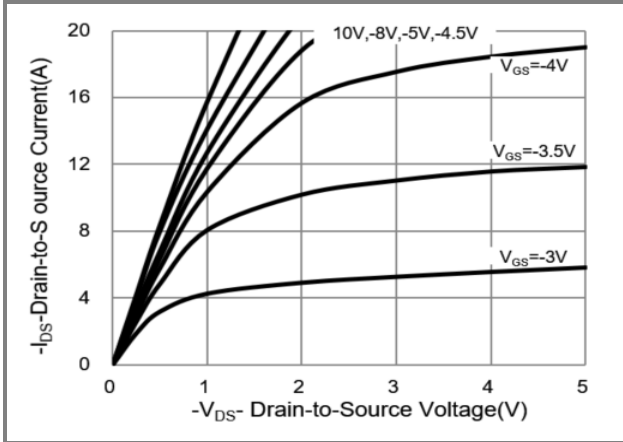


Fig.1 On-Region Characteristics

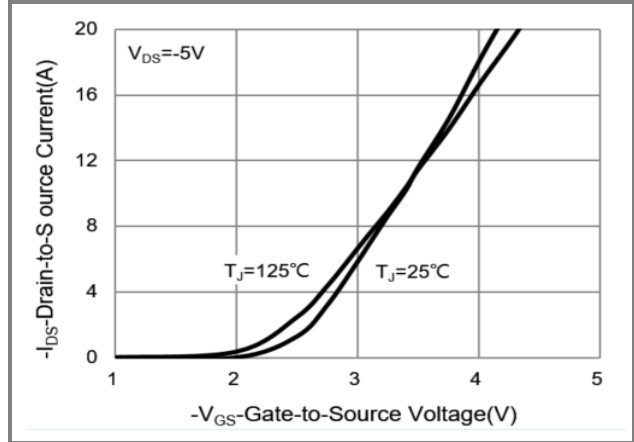


Fig.2 Transfer Characteristics

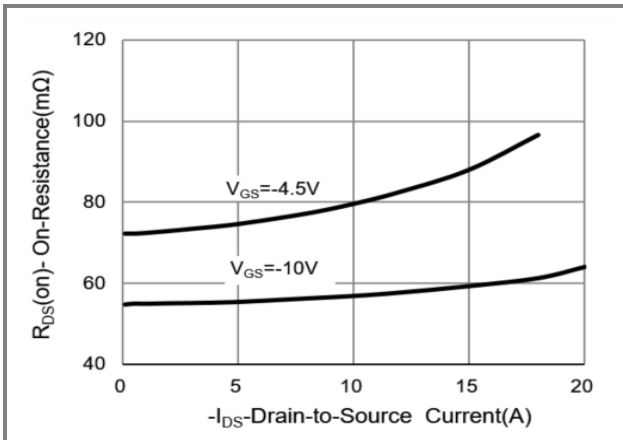


Fig.3 On-Resistance vs. Drain Current

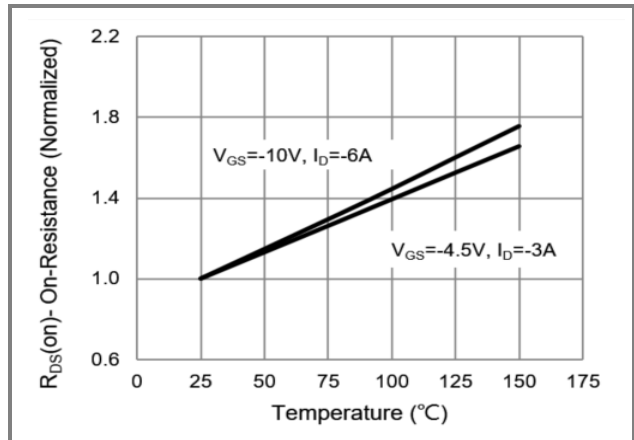


Fig.4 On-Resistance vs. Junction temperature

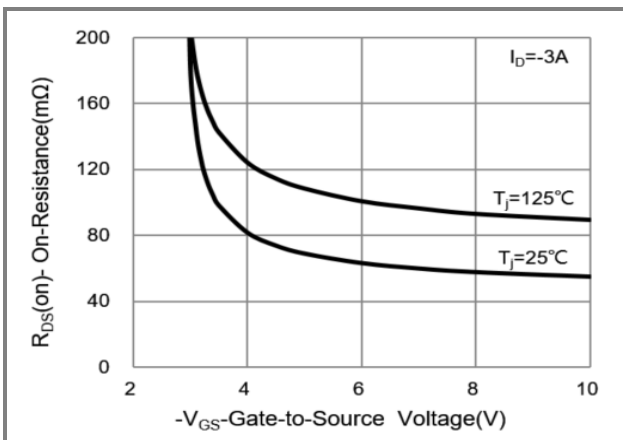


Fig.5 On-Resistance Variation with VGS.

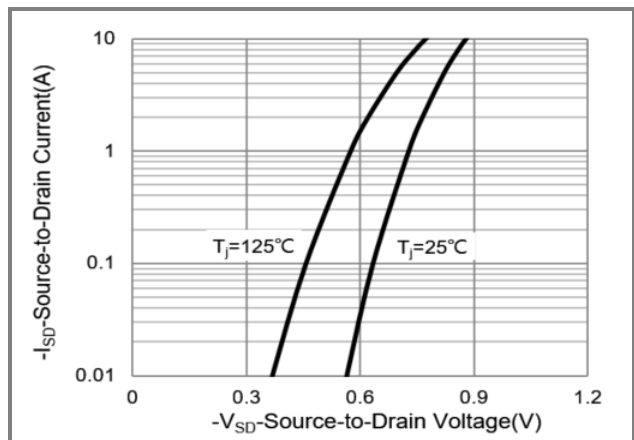


Fig.6 Source-Drain Diode Forward Voltage



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TYPICAL CHARACTERISTIC CURVES

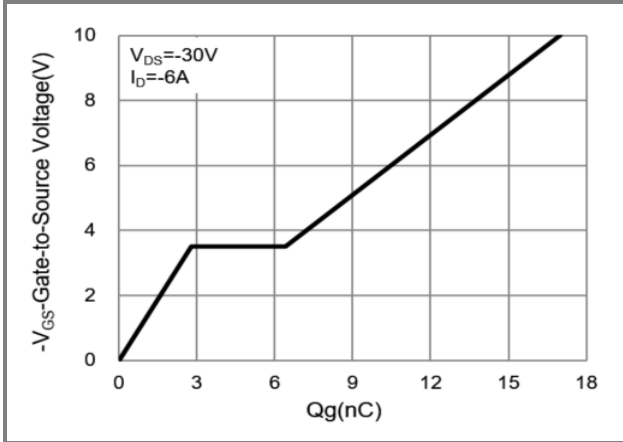


Fig.7 Gate-Charge Characteristics

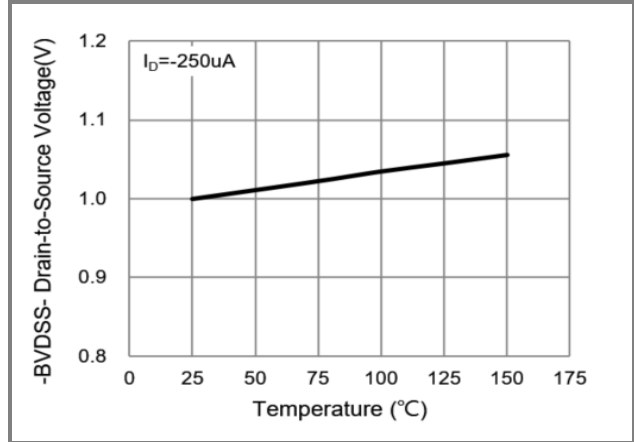


Fig.8 Breakdown Voltage Variation vs. Temperature.

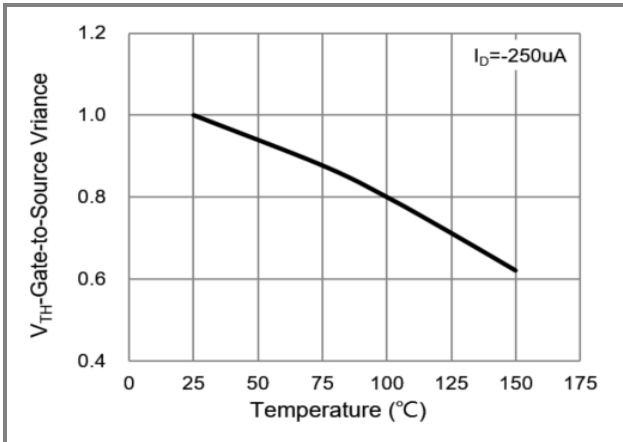


Fig.9 Threshold Voltage Variation with Temperature

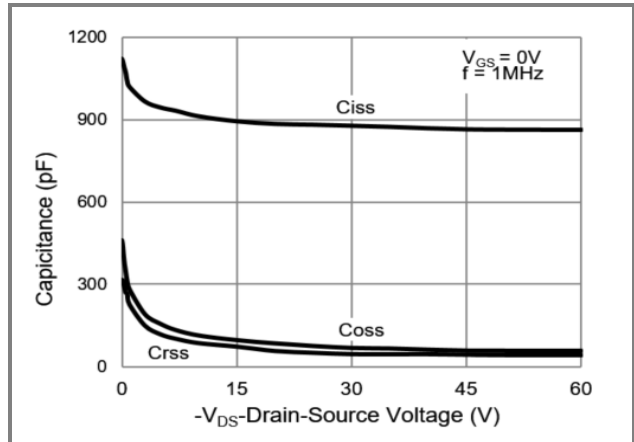


Fig.10 Capacitance vs. Drain-Source Voltage

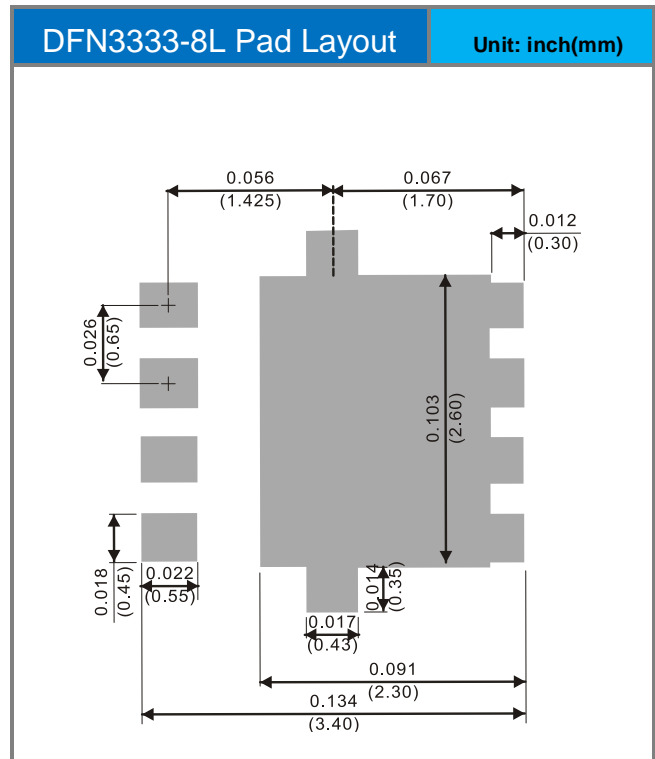
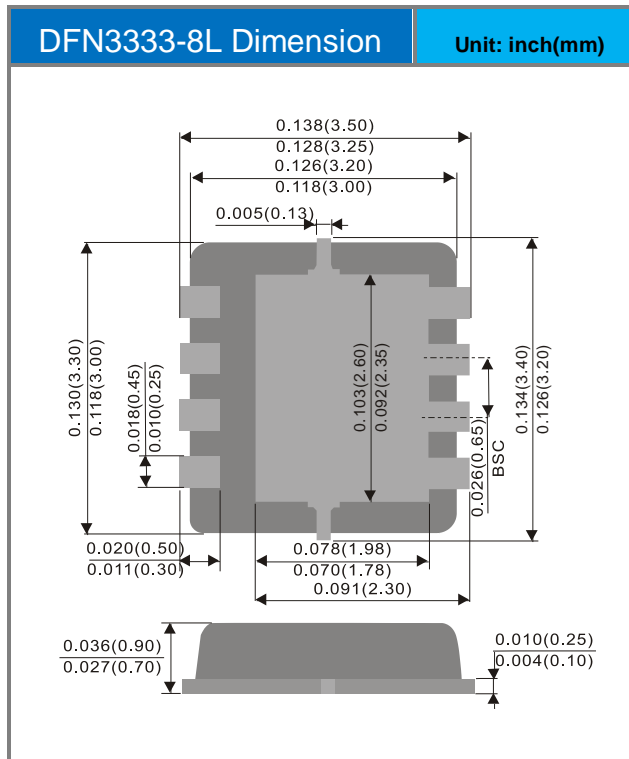


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PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ4463AP_R2_00001	DFN3333-8L	5K pcs / 13" reel	4463	Halogen free

Packaging Information & Mounting Pad Layout





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